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# **HRW1002A(S)**

Silicon Schottky Barrier Diode for Rectifying

**HITACHI**

ADE-208-207A (Z)

Rev. 1

Aug. 1994

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## **Features**

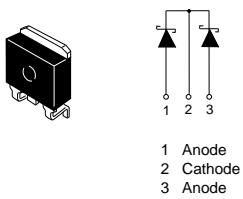
- Low forward voltage drop and suitable for high efficiency rectifying.
- Same power as TO-220AB.
- Small outline compared with TO-220AB.
- LDPAK(S) package is suitable for high density surface mounting.

## **Ordering Information**

Type No.	Laser Mark	Package Code
HRW1002A(S)	W1002A	LDPAK(S)

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## **Pin Arrangement**



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## HRW1002A(S)

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### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )<sup>\*</sup>

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}^{*2}$	20	V
Average forward current	$I_o^{*3}$	10	A
Non-Repetitive peak forward surge current	$I_{FSM}^{*4}$	75	A
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{STG}$	-40 to +125	$^\circ\text{C}$

Notes: 1. Per one device

2. See Fig.5

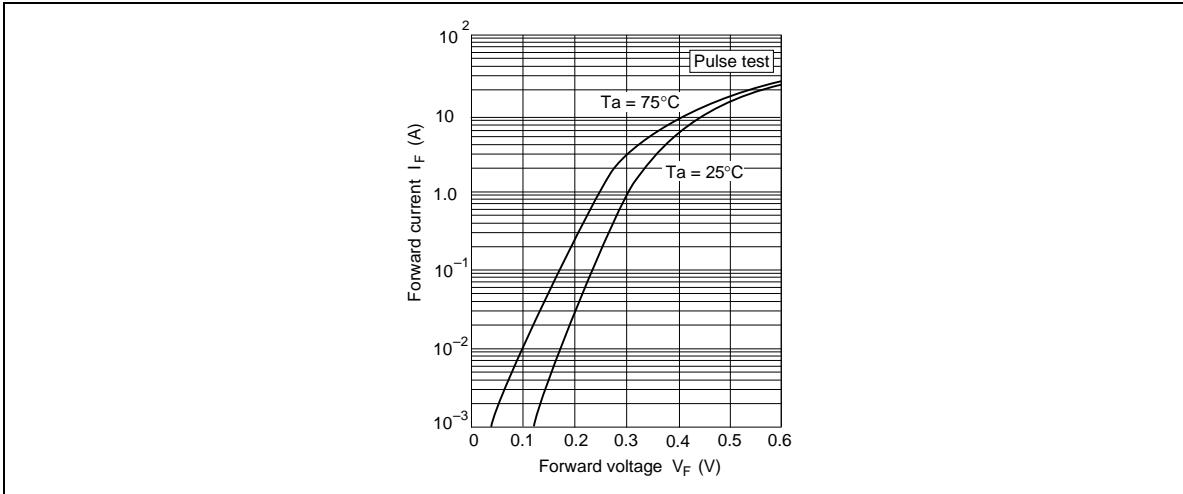
3. Square wave, Duty (1/2), Sum of two devices See Fig.4

4. Sine wave 10msec

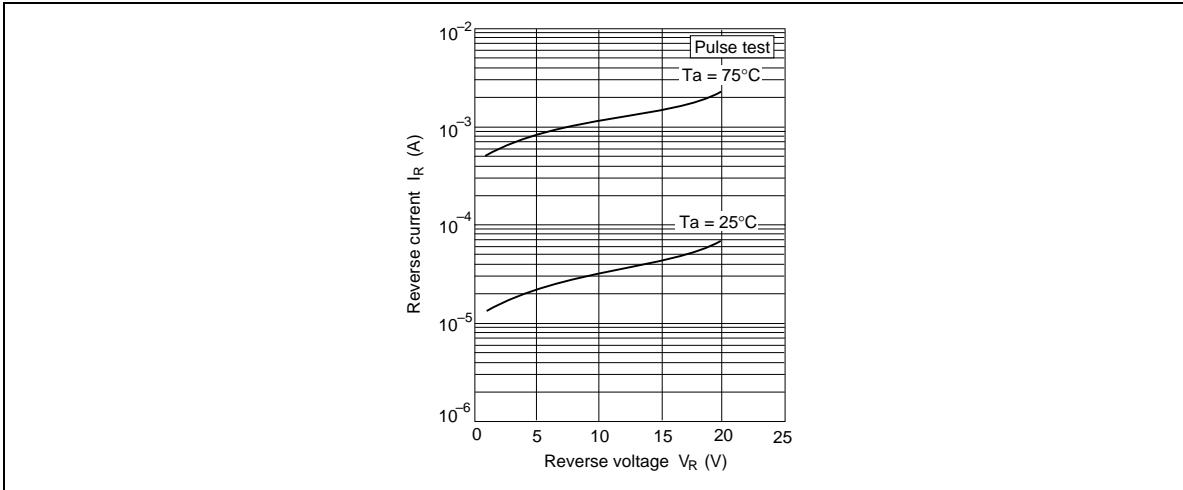
### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )<sup>\*</sup>

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	$V_F$	—	—	0.42	V	$I_F = 5.0\text{A}$
Reverse current	$I_R$	—	—	1.0	mA	$V_R = 20\text{V}$
ESD-capability	—	500	—	—	V	C = 200pF Both forward and reverse direction 1 pulse
Thermal resistance	$R_{th(j-c)}$	—	1.5	—	$^\circ\text{C/W}$	

Note: Per one device

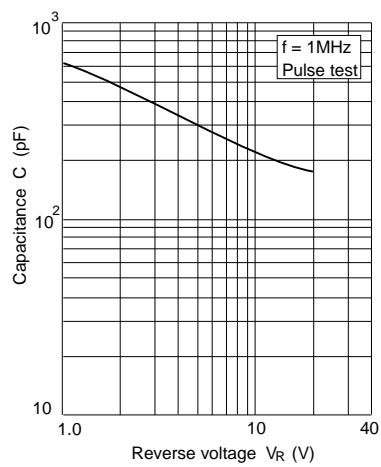


**Fig.1** Forward current Vs. Forward voltage

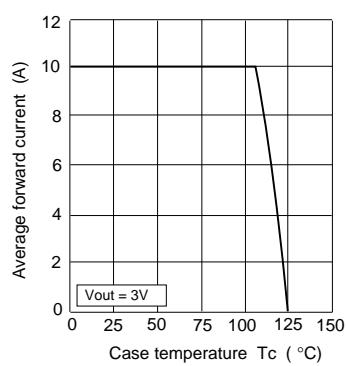


**Fig.2** Reverse current Vs. Reverse voltage

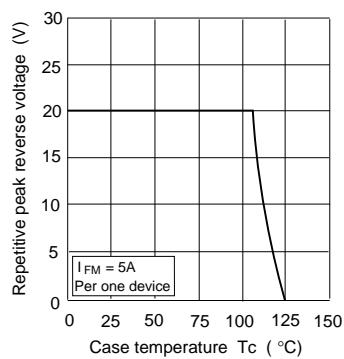
## **HRW1002A(S)**



**Fig.3 Capacitance Vs. Reverse voltage**



**Fig.4 Average forward current Vs. Case temperature**



**Fig.5 Repetitive peak reverse voltage Vs. Case temperature**

### Package Dimensions

